

Data Sheet January 2000 File Number 3572.3

100A, 600V Hyperfast Diode

The RHRU10060 is a hyperfast diode with soft recovery characteristics ($t_{rr} < 50$ ns). It has half the recovery time of ultrafast diodes and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA49069.

Ordering Information

PART NUMBER	PACKAGE	BRAND	
RHRU10060	TO-218	RHRU10060	

NOTE: When ordering, use the entire part number.

Symbol



Features

	Hyperfast with Soft Recovery	
•	Operating Temperature	175°C
•	Reverse Voltage	.600V

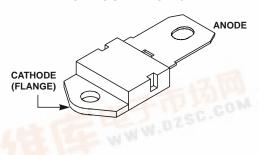
- Avalanche Energy Rated
- Planar Construction

Applications

- · Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-218



Absolute Maximum Ratings T_C = 25°C

	RHRU10060	UNITS
Peak Repetitive Reverse VoltageVRRM	600	V
Working Peak Reverse Voltage	600	V
DC Blocking Voltage	600	V
Average Rectified Forward Current	100	Z S G V
$(T_C = 60^{\circ}C)$		
Repetitive Peak Surge CurrentI _{FRM}	200	Α
(Square Wave, 20kHz)		
Nonrepetitive Peak Surge Current IFSM	1000	Α
(Halfwave, 1 Phase, 60Hz)		
Maximum Power Dissipation	210	W
Avalanche Energy (See Figures 7 and 8)	50	mJ
Operating and Storage Temperature	-65 to 175	οС



RHRU10060

 $\textbf{Electrical Specifications} \hspace{0.5cm} \textbf{T}_{C} = 25^{o}\text{C}, \hspace{0.1cm} \textbf{Unless Otherwise Specified}$

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V _F	I _F = 100A	-	-	2.1	V
	I _F = 100A, T _C = 150 ^o C	-	-	1.7	V
I _R	V _R = 600V	-	-	250	μΑ
	V _R = 600V, T _C = 150 ^o C	-	-	2.0	mA
t _{rr}	I _F = 1A, dI _F /dt = 100A/μs	-	-	50	ns
	I _F = 100A, dI _F /dt = 100A/μs	-	-	60	ns
t _a	I _F = 100A, dI _F /dt = 100A/μs	-	28	-	ns
t _b	I _F = 100A, dI _F /dt = 100A/μs	-	18	-	ns
$R_{ heta JC}$		-	-	0.71	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time (See Figure 6), summation of t_a + t_b .

t_a = Time to reach peak reverse current (See Figure 6).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

Typical Performance Curves

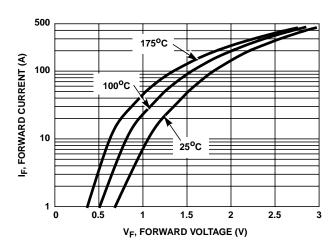


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

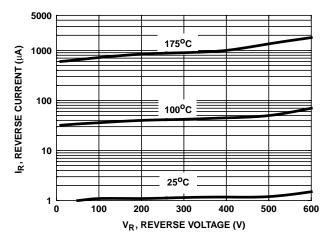


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

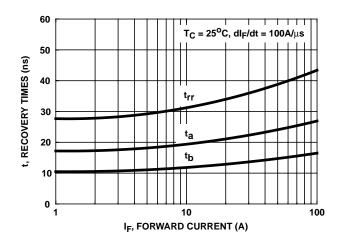


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

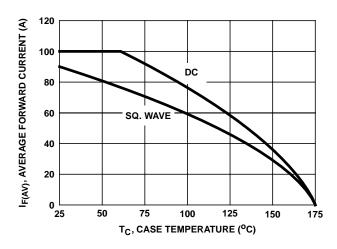


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

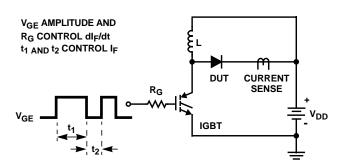


FIGURE 5. t_{rr} TEST CIRCUIT

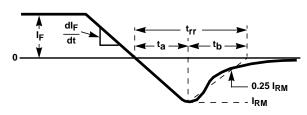


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

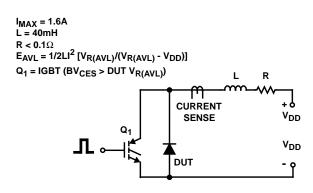


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

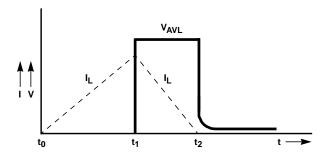


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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